DG441B, DG442B

Vishay Siliconix



Parameter		Symbol	Limit	Unit	
V+ to V-		1	44		
GND to V-			25	V	
Digital Inputs ^a , V _S , V _D			(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first		
Continuous Current (Any Termina	al)		30		
Current, S or D (Pulsed at 1 ms,	10 % duty cycle)		100		
Storage Temperature			- 65 to 125	°C	
	16-pin Plastic DIP ^c		470		
Power Dissipation (Package) ^b	16-pin Narrow Body SOIC ^d		900	mW	
	QFN-16 ^d		850	1	

- a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC Board.
- c. Derate 6 mW/°C above 75 °C.
- d. Derate 12 mW/°C above 75 °C.



SPECIFICATIONS ^a (for	dual supplies)							
		Test Conditions Unless Otherwise Specified V+ = 15 V, V- = - 15 V		Limits - 40 °C to 85 °C				
Parameter	Symbol	$V_L = 5 \text{ V}, V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^e$	Temp.b	Min. ^d Typ. ^c		Max. ^d	Unit	
Analog Switch								
Analog Signal Range ^e	V _{ANALOG}		Full	- 15		15	V	
Drain-Source On-Resistance	R _{DS(on)}	$I_S = 1 \text{ mA}, V_D = \pm 10 \text{ V}$	Room Full		45	80 95		
On-Resistance Match Between Channels ^e	$\Delta R_{DS(on)}$	$I_S = 1 \text{ mA}, V_D = \pm 10 \text{ V}$			2	4 5	Ω	
Switch Off Leakage Current	I _{S(off)}	$V_D = \pm 14 \text{ V}, V_S = \pm 14 \text{ V}$	Room Full	- 0.5 - 5	± 0.01	0.5 5		
	I _{D(off)}	ъ,	Room Full	- 0.5 - 5	± 0.01	0.5 5	nA	
Channel On Leakage Current	I _{D(on)}	$V_S = V_D = \pm 14 \text{ V}$	Room Full	- 0.5 - 10	± 0.02	0.5 10		
Digital Control								
Input Voltage Low	V _{INL}		Full			0.8	V	
Input Voltage High	V _{INH}		Full	2.4			-	
Input Current V _{IN} Low	I _{INL}	V _{IN} under test = 0.8 V All Other = 2.4 V	Full	- 1	- 0.01	1	μΑ	
Input Current V _{IN} High	I _{INH}	V _{IN} under test = 2.4 V All Other = 0.8 V	Full	- 1	0.01	1	μΑ	
Dynamic Characteristics								
Turn-On Time	t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Room		120	220	ns	
Turn-Off Time	t _{OFF}	$V_S = 10 V$, See Figure 2	Room		65	120	115	
Charge Injection ^e	Q	$C_L = 1 \text{ nF, } V_S = 0 \text{ V}$ $V_{gen} = 0 \text{ V, } R_{gen} = 0 \Omega$	Room		- 1		рС	
Off Isolation ^e	OIRR	$R_L = 50 \Omega$, $C_L = 15 pF$	Room		- 90		dB	
Crosstalk (Channel-to-Channel)	X _{TALK}	$V_S = 1 V_{RMS}$, $f = 100 kHz$	Room		- 95		aB	
SourceOff Capacitance ^e	C _{S(off)}	f = 1 MHz	Room		4			
Drain Off Capacitance ^e	C _{D(off)}	1 = 1 MHZ	Room		4		pF	
Channel On Capacitance ^e	C _{D(on)}	$V_S = V_D = 0 V$, $f = 1 MHz$	Room		16			
Power Supplies								
Positive Supply Current	l+	V+ = 16.5 V, V- = - 16.5 V	Room Full			1 5	μΑ	
Negative Supply Current	I-	V _{IN} = 0 or 5 V		- 1 - 5			μ,	



SPECIFICATIONS (for single supply)											
		Test Conditions Unless Otherwise Specified V+ = 12 V, V- = 0 V		Limits - 40 °C to 85 °C							
Parameter	Symbol	$V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{e}$	Temp.b	Min. ^d	Typ. ^c	Max. ^d	Unit				
Analog Switch											
Analog Signal Range ^e	V_{ANALOG}		Full	0		12	V				
Drain-Source On-Resistance	R _{DS(on)}	I _S = 1 mA, V _D = 3 V, 8 V	Room Full		90	160 200	Ω				
Dynamic Characteristics			•								
Turn-On Time	t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}, V_S = 8 \text{ V}$	Room		120	300	ns				
Turn-Off Time	t _{OFF}	See Figure 2	Room		60	200	115				
Charge Injection	Q	$C_L = 1 \text{ nF, } V_{gen} = 6 \text{ V, } R_{gen} = 0 \Omega$	Room		4		рC				
Power Supplies											
Positive Supply Current	l+	V _{IN} = 0 V or 5 V	Room Full			1 5	μΑ				
Negative Supply Current	l-	V _{IN} = 0 v oi 0 v	Room Full	- 1 - 5			μΑ				

Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SCHEMATIC DIAGRAM (typical channel)

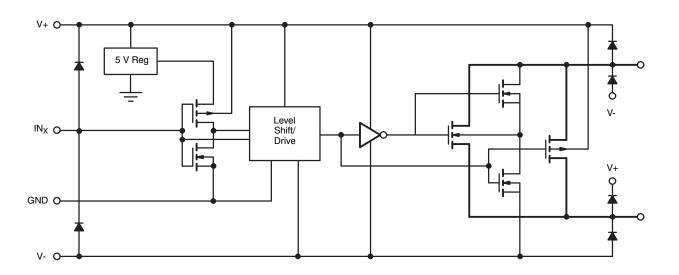
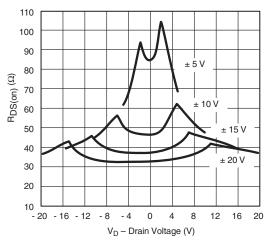


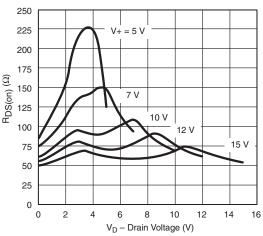
Figure 1.



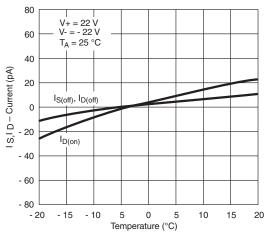
TYPICAL CHARACTERISTICS $(T_A = 25 \, ^{\circ}\text{C}, \text{ unless otherwise noted})$



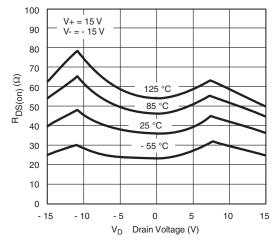
 $R_{DS(on)}$ vs. V_D and Power Supply Voltages



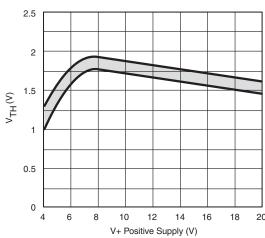
R_{DS(on)} vs. V_D and Single Power Supply Voltages



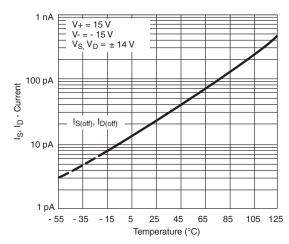
Leakage Currents vs. Analog Voltage



 $R_{DS(on)}$ vs. V_D and Temperature

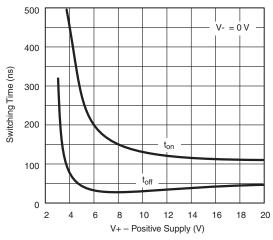


Input Switching Threshold vs. Supply Voltage

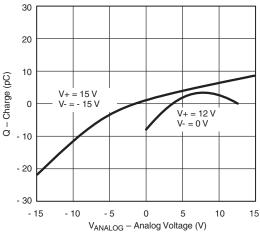


Leakage Currents vs. Temperature

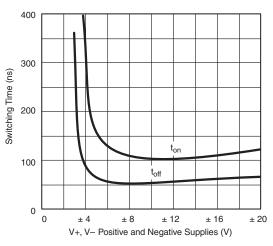
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



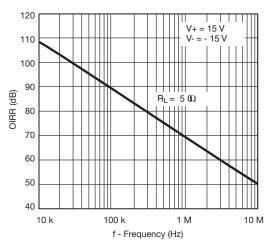
Switching Time vs. Single Supply Voltage



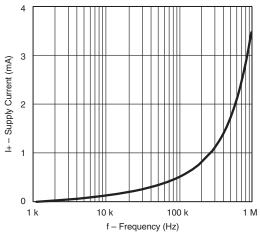
 $\mathbf{Q_S},\,\mathbf{Q_D}$ - Charge Injection vs. Analog Voltage



Switching Times vs. Power Supply Voltage



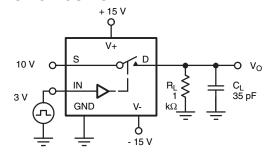
Off Isolation vs. Frequency



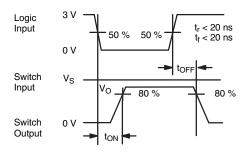
Supply Current vs. Switching Frequency



TEST CIRCUITS

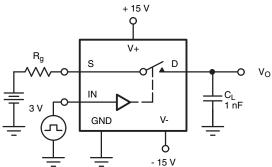


C_L (includes fixture and stray capacitance)



Note: Logic input waveform is inverted for DG442.

Figure 2. Switching Time



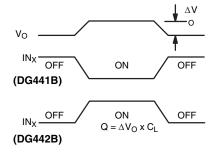
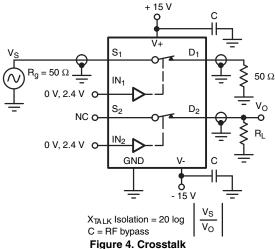


Figure 3. Charge Injection

C = 1 mF tantalum in parallel with 0.01 mF ceramic



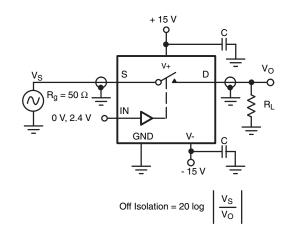


Figure 5. Off Isolation

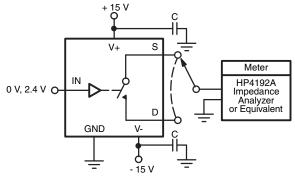
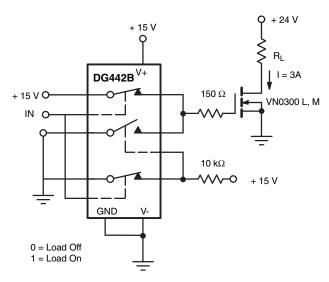


Figure 6. Source/Drain Capacitances

APPLICATIONS





+ 15 V V_{IN} 1/4 DG442B S D V_{OUT} IN O - 15 V H = Sample L = Hold

Figure 7. Power MOSFET Driver

Figure 8. Open Loop Sample-and-Hold

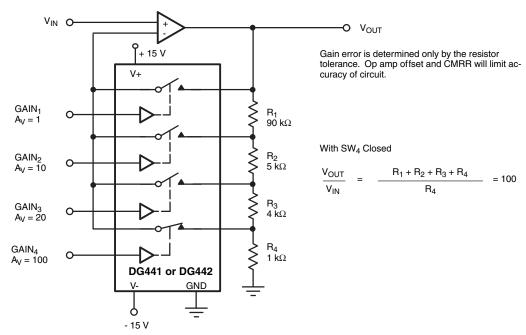
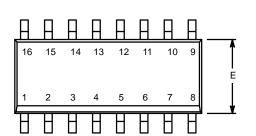


Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72625.



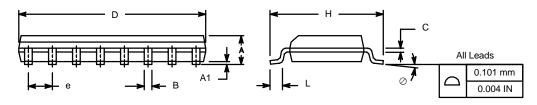
SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012



	MILLIM	IETERS	INC	HES					
Dim	Min	Max	Min	Max					
Α	1.35	1.75	0.053	0.069					
A ₁	0.10	0.20	0.004	0.008					
В	0.38	0.51	0.015	0.020					
С	0.18	0.23	0.007	0.009					
D	9.80	10.00	0.385	0.393					
E	3.80	4.00	0.149	0.157					
е	1.27	BSC	0.050	BSC					
Н	5.80	6.20	0.228	0.244					
L	0.50	0.93	0.020	0.037					
0	0°	8°	0°	8°					
FCN: S-03946—Rev F 09-Jul-01									

ECN: S-03946—Rev. F, 09-Jul-01

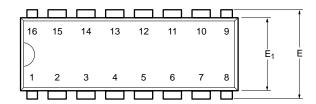
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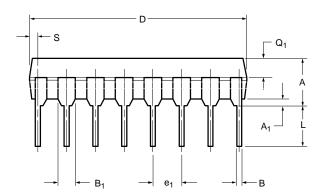


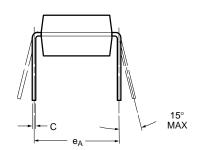
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PDIP: 16-LEAD



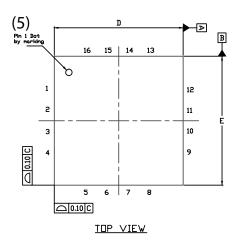


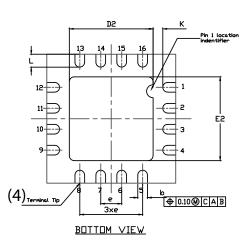


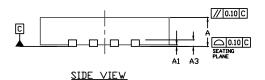
	MILLIM	IETERS	INC	HES			
Dim	Min	Max	Min	Max			
Α	3.81	5.08	0.150	0.200			
A ₁	0.38	1.27	0.015	0.050			
В	0.38	0.51	0.015	0.020			
B ₁	0.89	1.65	0.035	0.065			
С	0.20	0.30	0.008	0.012			
D	18.93	21.33	0.745	0.840			
Е	7.62	8.26	0.300	0.325			
E ₁	5.59	7.11	0.220	0.280			
e ₁	2.29	2.79	0.090	0.110			
e _A	7.37	7.87	0.290	0.310			
L	2.79	3.81	0.110	0.150			
Q_1	1.27	2.03	0.050	0.080			
S	0.38	1.52	.015	0.060			
ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482							

Document Number: 71261 www.vishay.com 06-Jul-01 sum.vishay.com

QFN 4x4-16L Case Outline







	VARIATION 1					VARIATION 2							
DIM	МІ	MILLIMETERS ⁽¹⁾		INCHES		MILLIMETERS ⁽¹⁾		S ⁽¹⁾		INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
Α	0.75	0.85	0.95	0.029	0.033	0.037	0.75	0.85	0.95	0.029	0.033	0.037	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
A3		0.20 ref.		0.008 ref.		0.20 ref.			0.008 ref.				
b	0.25	0.30	0.35	0.010	0.012	0.014	0.25	0.30	0.35	0.010	0.012	0.014	
D		4.00 BSC		0.157 BSC		4.00 BSC		0.157 BSC					
D2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106	
е	0.65 BS0				0.026 BSC		0.65 BSC				0.026 BSC		
Е	4.00 BSC		0.157 BSC		4.00 BSC		0.157 BSC						
E2	2.0	2.1	2.2	0.079	0.083	0.087	2.5	2.6	2.7	0.098	0.102	0.106	
K		0.20 min			0.008 min.		0.20 min. 0.008		0.008 min.				
L	0.5	0.6	0.7	0.020	0.024	0.028	0.3	0.4	0.5	0.012	0.016	0.020	
N ⁽³⁾		16		16 16			16						
Nd ⁽³⁾		4			4	4 4							
Ne ⁽³⁾		4			4		4 4						

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

ECN: S13-0893-Rev. B, 22-Apr-13

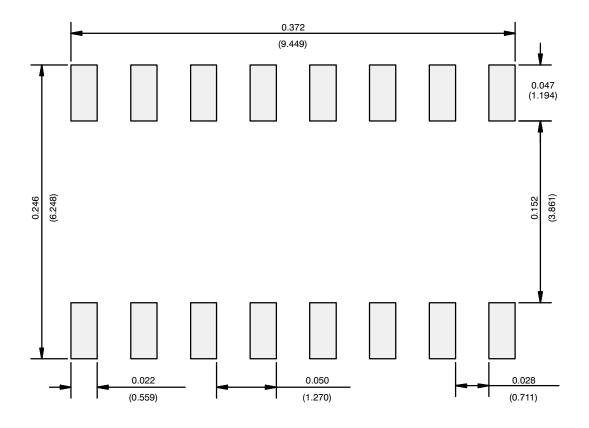
DWG: 5890

Revision: 22-Apr-13

Document Number: 71921



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE

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